





20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D max T _A = +25°C	
	175mΩ @ V_{GS} = 4.5 V	1.30A	
20V	240mΩ @ V _{GS} = 2.5V	1.11A	
	$360 \text{m}\Omega$ @ V_{GS} = 1.8 V	0.91A	

Features and Benefits

- Footprint of just 0.6mm² thirteen times smaller than SOT23
- 0.5mm profile ideal for low profile applications
- On resistance <200mΩ @ V_{GS} = 4.5V
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate 2KV
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

Mechanical Data

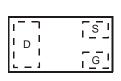
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.001 grams (Approximate)



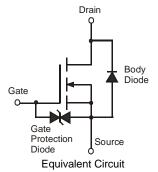




Bottom View



Top View Internal Schematic



Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2300UFB-7	NI	7	8	3,000
DMN2300UFB-7B	NI	7	8	10.000

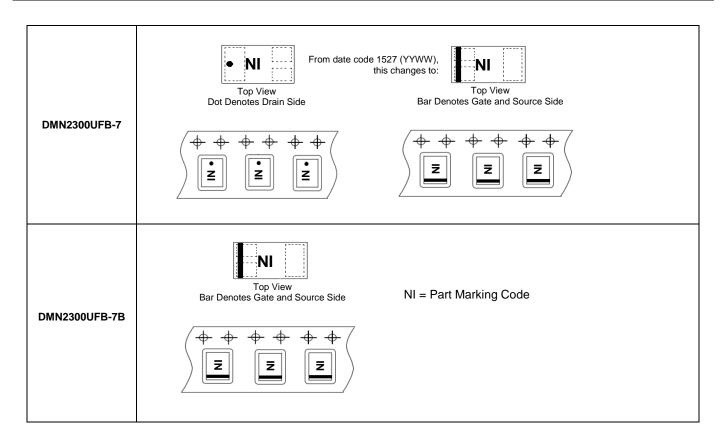
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.





Marking Information







Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current	Steady State	$T_A = +25^{\circ}\text{C (Note 5)}$ $T_A = +85^{\circ}\text{C (Note 5)}$ $T_A = +25^{\circ}\text{C (Note 6)}$	I _D	1.32 0.94 1.78	А
Pulsed Drain Current (Note 7)		I _{DM}	8	Α	

Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.468	W
Power Dissipation (Note 6)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	267	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	104	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

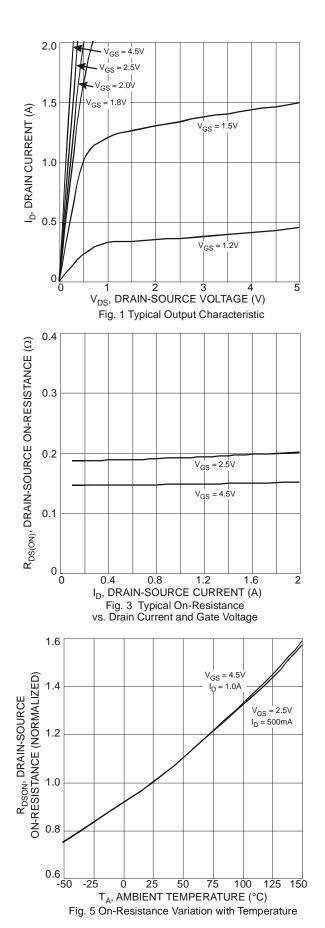
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	ı	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	0.45	-	0.95	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		-	ı	175		$V_{GS} = 4.5V, I_D = 300mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	ı	240	mΩ	$V_{GS} = 2.5V, I_D = 250mA$	
		-	-	360		$V_{GS} = 1.8V, I_D = 100mA$	
Forward Transfer Admittance	Y _{fs}	40	-	-	mS	$V_{DS} = 3V, I_{D} = 30mA$	
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS	•						
Input Capacitance	Ciss	-	67.62	-	pF	T.,	
Output Capacitance	Coss	-	9.74	-	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	7.58	-	pF		
Gate Resistance	Rg	-	68.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	-	0.89	-	nC	V 45V V 40V	
Gate-Source Charge	Qgs	-	0.14	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 1A$	
Gate-Drain Charge	Q _{qd}	-	0.16	-	nC		
Turn-On Delay Time	t _{D(on)}	-	4.92	-	ns		
Turn-On Rise Time	t _r	-	6.93	-	ns	$V_{DS} = 10V, I_{D} = 1A$ $V_{GS} = 4.5V, R_{G} = 6\Omega$	
Turn-Off Delay Time	t _{D(off)}	-	21.71	-	ns		
Turn-Off Fall Time	t _f	-	10.62	-	ns		

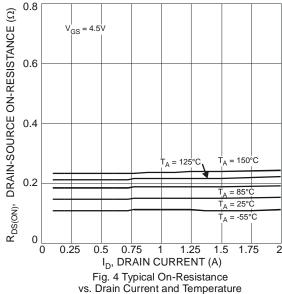
Notes:

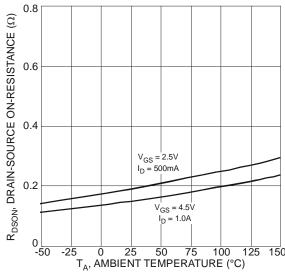
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm X 25mm square copper plate.
- 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 8. Short duration pulse test used to minimize self-heating effect.





2.0 $V_{DS} = 5V$ 1.5 $V_{DS} = 5V$ 1.0 V_{DS}







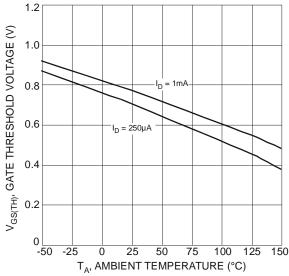
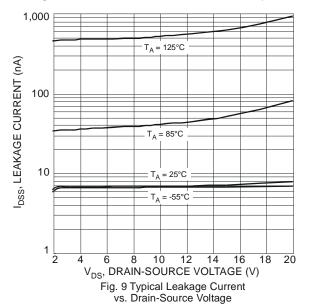
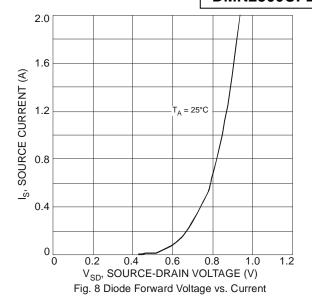


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



8 (S) 6 V_{DS} = 15V V_{DS} = 15V V_{DS} = 1A V_{DS} = 15V V_{DS}



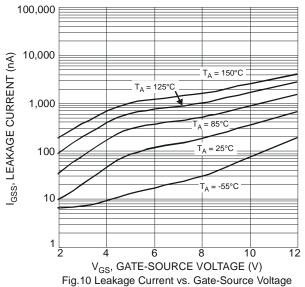


Fig. 11 Gate-Charge Characteristics



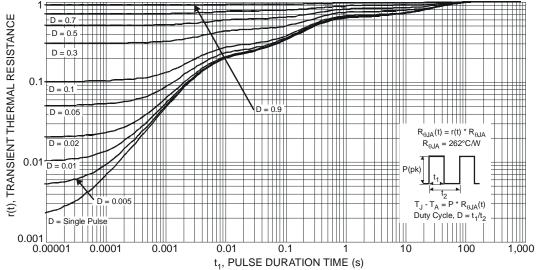
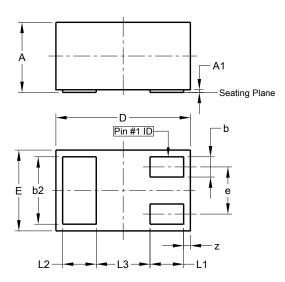


Fig. 12 Transient Thermal Response



Package Outline Dimensions

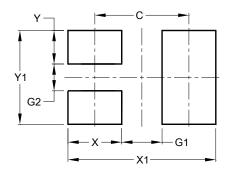
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	1	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70





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